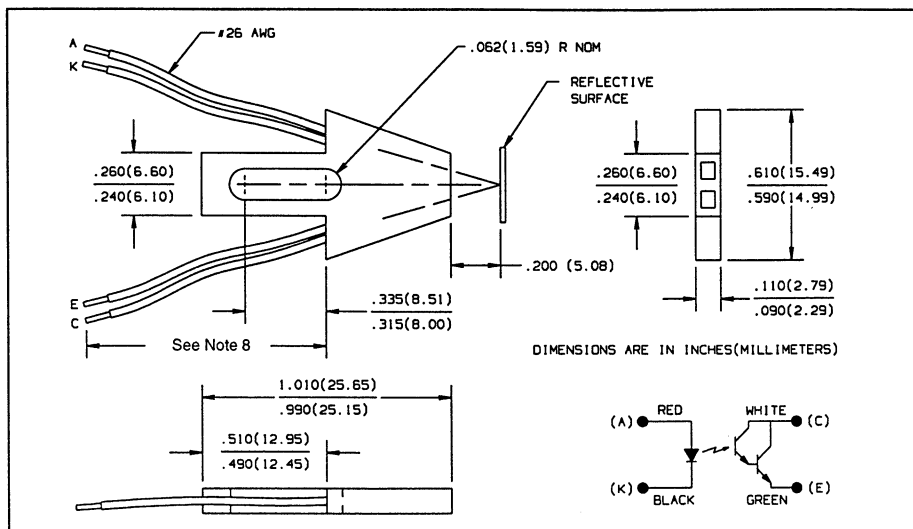
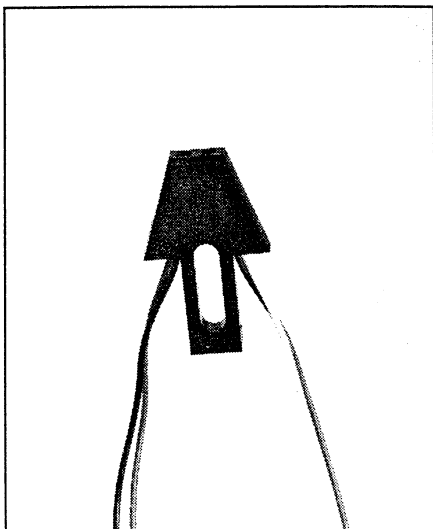


Reflective Object Sensor **Type OPB701, OPB701AL**



Features

- Photodarlington output
- Low profile to facilitate stacking
- Low cost plastic housing
- 4.0 inch minimum length lead wire (OPB701)
- 18.0 inch minimum length lead wire (OPB701AL)

Description

The OPB701 series consists of an infrared emitting diode and an NPN silicon photodarlington mounted "side-by-side" on converging optical axes, in a black plastic housing. The photodarlington responds to radiation from the emitter only when a reflective object passes within its field of view.

Leads are #26 AWG, teflon insulation, 4.0" minimum length (OPB701) or 18.0" minimum length (OPB701AL), stripped and tinned.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Storage Temperature Range	-40° C to +125° C
Operating Temperature Range	-40° C to +100° C

Input Diode

Continuous Forward Current	100 mA
Reverse Voltage	2.0 V
Power Dissipation	80 mW ⁽¹⁾

Output Photodarlington

Collector-Emitter Voltage	15 V
Emitter-Collector Voltage	5.0 V
Power Dissipation	50 mW ⁽²⁾

Notes:

- (1) Derate linearly 1.07 mW/° C above 25° C.
- (2) Derate linearly 0.67 mW/° C above 25° C.
- (3) Measured using Eastman Kodak neutral white test card with 90% diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog #1257795
- (4) Crosstalk (I_{cx}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.
- (5) d is the distance from the assembly head to the reflective surface.
- (6) Lower curve is based on a calculated worst case condition rather than the conventional -2σ limit.
- (7) All parameters tested using pulse technique.
- (8) 4.0" (101.6 mm) min for OPB701, 18.0" (457.2 mm) min for OPB701AL.



For RoHS compliant devices add "Z" to the end of the part number: OPB701Z, OPB701ALZ

Type OPB701, OPB701AL

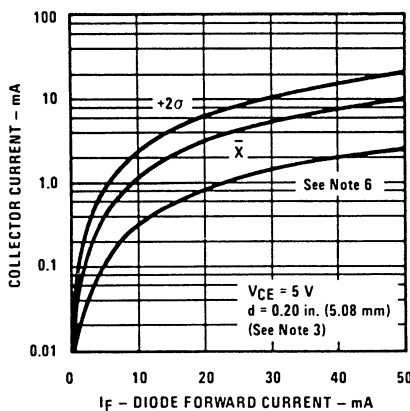
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
Input Diode					
V_F	Forward Voltage		1.70	V	$I_F = 50\text{ mA}$
I_R	Reverse Current		100	μA	$V_R = 2.0\text{ V}$
Output Photodarlington					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	15		V	$I_C = 100\text{ }\mu\text{A}$
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5.0		V	$I_E = 100\text{ }\mu\text{A}$
I_{CEO}	Collector Dark Current		1.00	nA	$V_{CE} = 10\text{ V}$, $I_F = 0$, $E_e = \leq 0.100\text{ }\mu\text{W}/\text{cm}^2$
Combined					
$I_{C(ON)}$	On-State Collector Current	2.0		mA	$V_{CE} = 5\text{ V}$, $I_F = 40\text{ mA}$, $d = 0.200\text{ in. (5.08 mm)}$ ⁽³⁾⁽⁵⁾
I_{CX}	Crosstalk		20	μA	$V_{CE} = 5\text{ V}$, $I_F = 40\text{ mA}$, No Reflecting Surface ⁽⁴⁾
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage		1.10	V	$I_F = 40\text{ mA}$, $I_C = 1.0\text{ mA}$, $d = 0.200\text{ in. (5.08 mm)}$ ⁽³⁾⁽⁵⁾

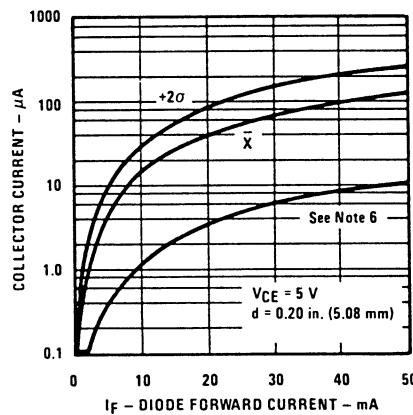
REFLECTIVE
OBJECT
SENSORS

Typical Performance Curves

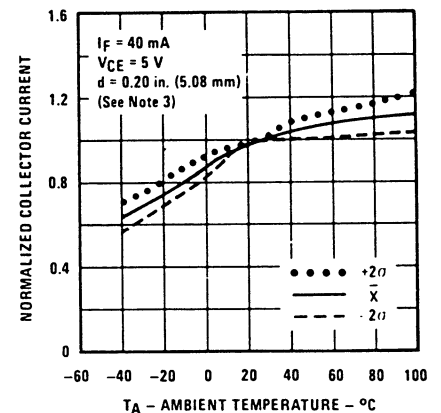
Reflective Surface Collector Current
vs. Diode Forward Current



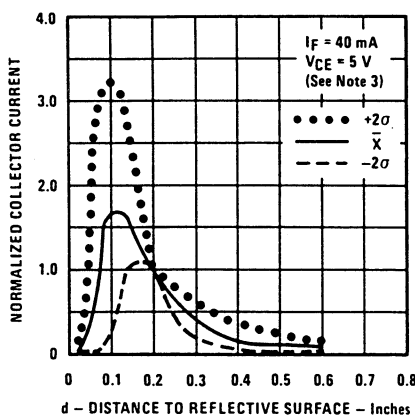
Diffused Surface Collector Current
vs. Diode Forward Current



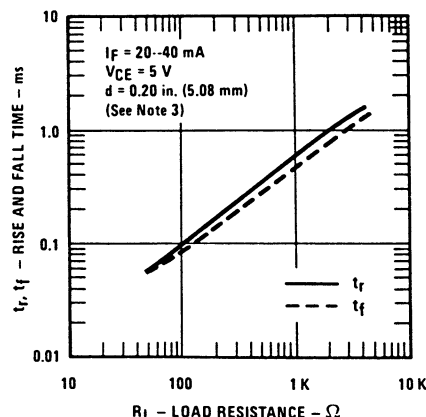
Normalized Collector Current
vs. Ambient Temperature



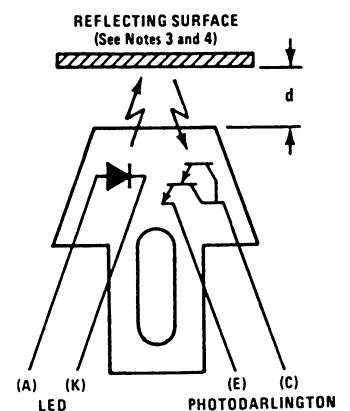
Normalized Collector Current
vs. Object Distance



Rise and Fall Time vs.
Load Resistance



Test Condition



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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